

HBR10200S

主要参数 MAIN CHARACTERISTICS

$I_{F(AV)}$	10 (2×5) A
V_{RRM}	200 V
T_j	175 °C
$V_{F(max)}$	0.75V (@ $T_j=125^{\circ}C$)

用途

- 高频开关电源
- 低压续流电路和保护电路

APPLICATIONS

- High frequency switch power supply
- Free wheeling diodes, polarity protection applications

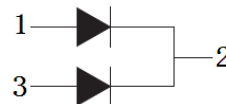
产品特性

- 共阴结构
- 低功耗，高效率
- 良好的高温特性
- 有过压保护环，高可靠性
- 环保（RoHS）产品

FEATURES

- Common cathode structure
- Low power loss, high efficiency
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability
- RoHS product

封装 Package



T0-263



绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^{\circ}\text{C}$)

项 目 Parameter		符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage		V_{RRM}	200	V
最大直流阻断电压 Maximum DC blocking voltage		V_{DC}	200	V
正向平均整流电流 Average forward current	整个器件 per device 单 侧 per diode	$I_{F(AV)}$	10	A
			5	
正向峰值浪涌电流 Surge non repetitive forward current (额定负载 8.3ms 半正弦波—按 JEDEC 方法) 8.3 ms single half-sine-wave (JEDEC Method)		I_{FSM}	125	A
最高结温 Maximum junction temperature		T_j	175	$^{\circ}\text{C}$
储存温度 Storage temperature range		T_{STG}	-40~+150	$^{\circ}\text{C}$

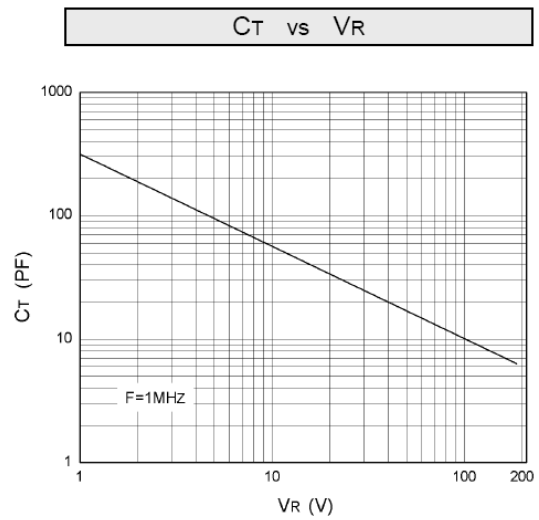
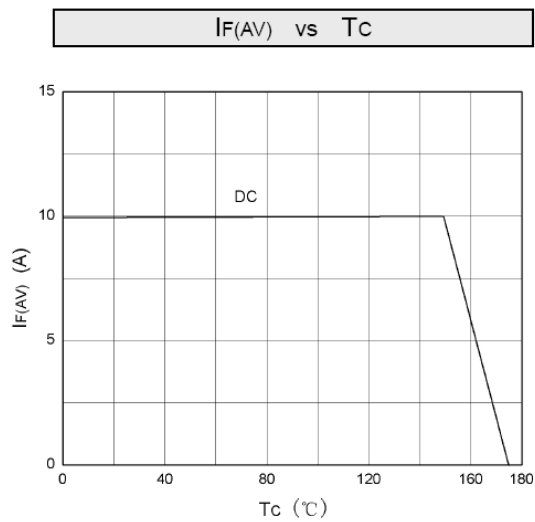
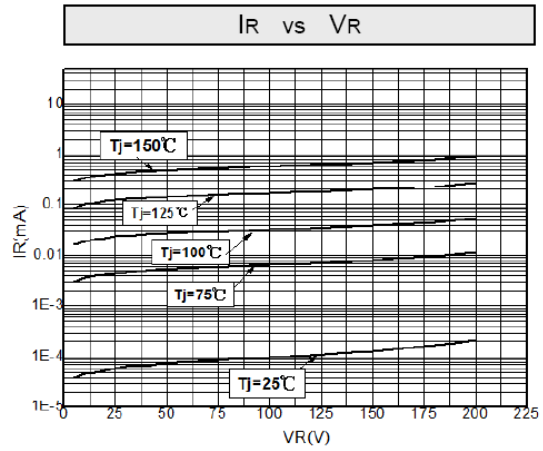
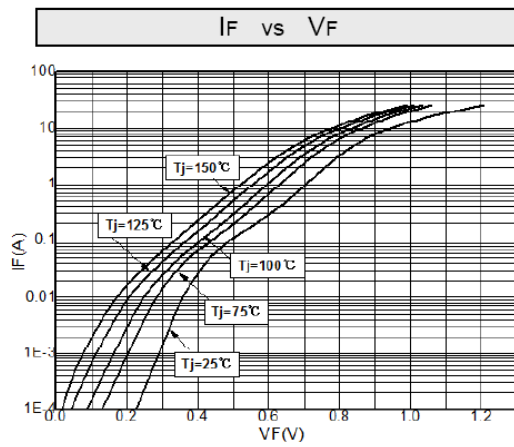
电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单位 Unit
I_R	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$	-	-	10	μA
	$T_j = 125^{\circ}\text{C}$		-	-	5	mA
V_F	$T_j = 25^{\circ}\text{C}$	$I_F = 5\text{A}$	-	0.85	0.93	V
	$T_j = 125^{\circ}\text{C}$		-	0.71	0.75	V
V_F	$T_j = 25^{\circ}\text{C}$	$I_F = 10\text{A}$	-	0.94	0.98	V
	$T_j = 125^{\circ}\text{C}$		-	0.81	0.86	V

热特性 THERMAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	最小值 Value(min)	最大值 Value(max)	单 位 Unit
结到管壳的热阻 Thermal resistance from junction to case	$R_{th(j-c)}$	-	1.9	$^{\circ}\text{C/W}$

特征曲线 ELECTRICAL CHARACTERISTICS (curves)



外形尺寸 PACKAGE MECHANICAL DATA

TO-263

